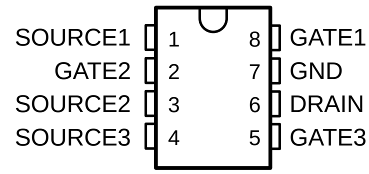
- **Low $r_{DS(on)}$ . . . 0.6 Ω Typ**
- **High-Voltage Outputs . . . 60 V**
- **Pulsed Current . . . 2.25 A Per Channel**
- **Fast Commutation Speed**
- **Direct Logic-Level Interface**

D PACKAGE
(TOP VIEW)

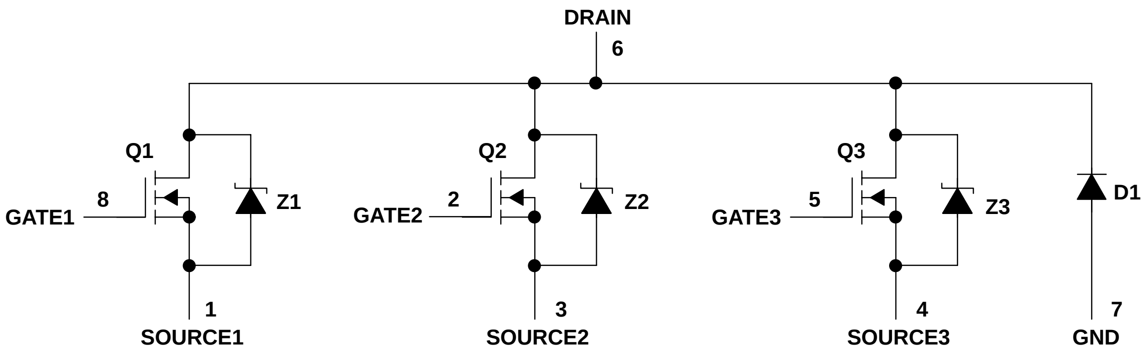


description

The TPIC3322L is a monolithic logic-level power DMOS transistor array that consists of three isolated N-channel enhancement-mode DMOS transistors configured with a common drain and open sources.

The TPIC3322L is offered in a standard 8-pin small-outline surface-mount (D) package and is characterized for operation over the case temperature range of –40°C to 125°C.

schematic diagram



absolute maximum ratings over operating case temperature range (unless otherwise noted)†

Drain-to-source voltage, V_{DS}	60 V
Source-to-GND voltage	100 V
Drain-to-GND voltage	100 V
Gate-to-source voltage, V_{GS}	±20 V
Continuous drain current, each output, all outputs on, T_C = 25°C	0.75 A
Continuous source-to-drain diode current, T_C = 25°C	0.75 A
Pulsed drain current, each output, I_{max}, T_C = 25°C (see Note 1 and Figure 15)	2.25 A
Single-pulse avalanche energy, E_{AS}, T_C = 25°C (see Figure 4)	19 mJ
Continuous total power dissipation at (or below) T_C = 25°C (see Figure 15)	0.95 W
Operating virtual junction temperature range, T_J	–40°C to 150°C
Operating case temperature range, T_C	–40°C to 125°C
Storage temperature range, T_{stg}	–65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: Pulse duration = 10 ms and duty cycle = 2%.

electrical characteristics, T_C = 25°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
$V_{(BR)DSX}$	Drain-to-source breakdown voltage	I_D = 250 µA, V_{GS} = 0		60			V
$V_{GS(th)}$	Gate-to-source threshold voltage	I_D = 1 mA, $V_{DS} = V_{GS}$		1.5	1.85	2.2	V
$V_{(BR)}$	Reverse drain-to-GND breakdown voltage (across D1)	Drain-to-GND current = 250 µA		100			V
$V_{DS(on)}$	Drain-to-source on-state voltage	I_D = 0.75 A, V_{GS} = 5 V, See Notes 2 and 3			0.45	0.53	V
V_F	Forward on-state voltage, GND-to-drain	I_D = 0.75 A, See Notes 2 and 3			1.8		V
$V_{F(SD)}$	Forward on-state voltage, source-to-drain	I_S = 0.75 A, V_{GS} = 0, See Notes 2 and 3 and Figure 12			0.85	1	V
I_{DSS}	Zero-gate-voltage drain current	V_{DS} = 48 V, V_{GS} = 0	T_C = 25°C		0.05	1	µA
			T_C = 125°C		0.5	10	
I_{GSSF}	Forward gate current, drain short circuited to source	V_{GS} = 16 V, V_{DS} = 0			10	100	nA
I_{GSSR}	Reverse gate current, drain short circuited to source	V_{SG} = 16 V, V_{DS} = 0			10	100	nA
I_{lkg}	Leakage current, drain-to-GND	V_{DGND} = 48 V	T_C = 25°C		0.05	1	µA
			T_C = 125°C		0.5	10	
$r_{DS(on)}$	Static drain-to-source on-state resistance	V_{GS} = 5 V, I_D = 0.75 A, See Notes 2 and 3 and Figures 6 and 7	T_C = 25°C		0.6	0.7	Ω
			T_C = 125°C		0.94	1	
g_{fs}	Forward transconductance	V_{DS} = 10 V, I_D = 0.5 A, See Notes 2 and 3 and Figure 9		0.75	0.9		S
C_{iss}	Short-circuit input capacitance, common source	V_{DS} = 25 V, V_{GS} = 0, f = 1 MHz, See Figure 11			115	145	pF
C_{oss}	Short-circuit output capacitance, common source				60	75	
C_{rss}	Short-circuit reverse transfer capacitance, common source				30	40	

NOTES: 2. Technique should limit $T_J – T_C$ to 10°C maximum.
3. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.

source-to-drain and GND-to-drain diode characteristics, T_C = 25°C

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
$t_{rr(SD)}$	Reverse-recovery time	I_S = 0.375 A, V_{GS} = 0, di/dt = 100 A/µs, V_{DS} = 48 V, See Figures 1 and 14	Z1, Z2, Z3		30		ns
			D1		85		
Q_{RR}	Total diode charge		Z1, Z2, Z3		0.03		µC
			D1		0.19		

resistive-load switching characteristics, T_C = 25°C

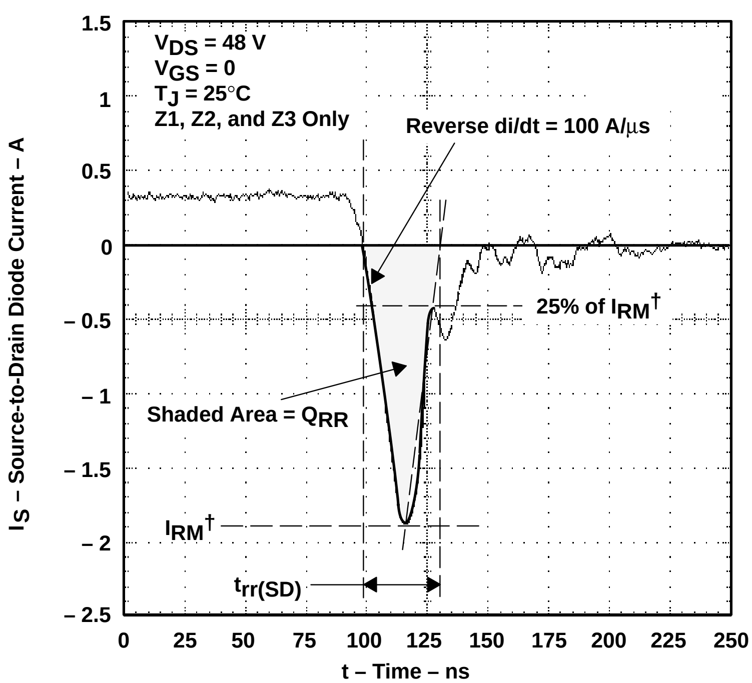
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_{d(on)}$	Turn-on delay time	V_{DD} = 25 V, R_L = 67 Ω, t_{r1} = 10 ns, t_{f1} = 10 ns, See Figure 2		8	16	ns
$t_{d(off)}$	Turn-off delay time			12	24	
t_{r2}	Rise time			14	28	
t_{f2}	Fall time			13	26	
Q_g	Total gate charge	V_{DS} = 48 V, I_D = 0.375 A, V_{GS} = 5 V, See Figure 3		1.8	2.3	nC
$Q_{gs(th)}$	Threshold gate-to-source charge			0.4	0.5	
Q_{gd}	Gate-to-drain charge			1.1	1.4	
L_D	Internal drain inductance			5		nH
L_S	Internal source inductance			5		
R_g	Internal gate resistance			0.25		Ω

thermal resistance

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance, See Note 4	All outputs with equal power		130		°C/W
$R_{\theta JC}$	Junction-to-case thermal resistance			44		

NOTE 4: Package mounted on an FR4 printed-circuit board with no heat sink.

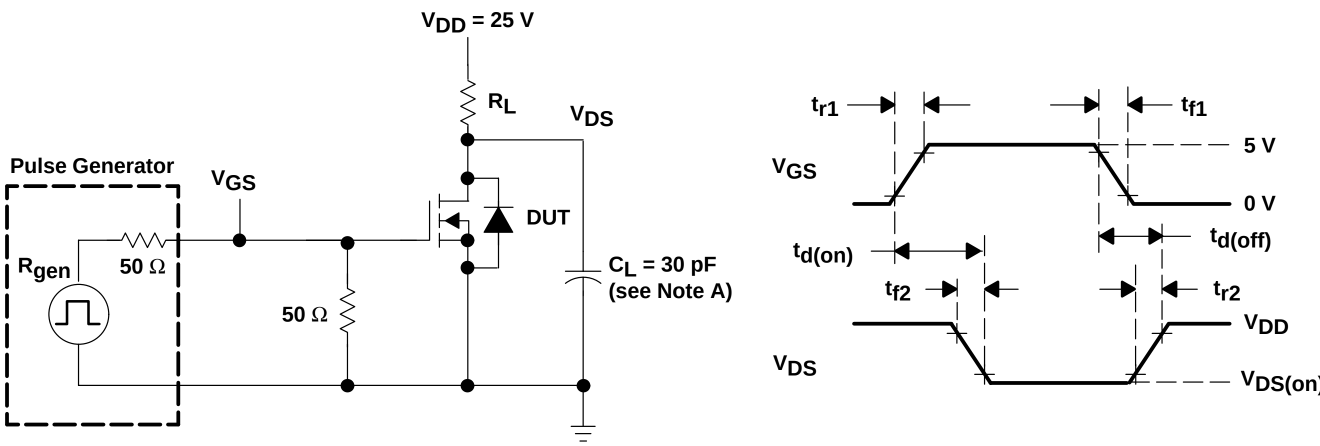
PARAMETER MEASUREMENT INFORMATION



† I_{RM} = maximum recovery current
NOTE A. The above waveform represents D1 in shape only.

Figure 1. Reverse-Recovery-Current Waveform of Source-to-Drain Diode

PARAMETER MEASUREMENT INFORMATION

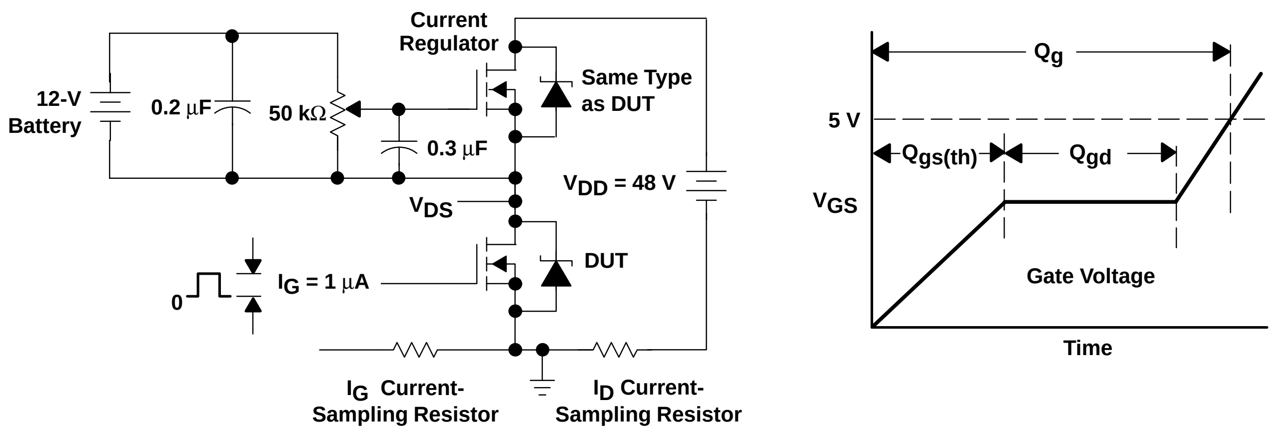


TEST CIRCUIT

VOLTAGE WAVEFORMS

NOTE A: C_L includes probe and jig capacitance.

Figure 2. Resistive-Switching Test Circuit and Voltage Waveforms

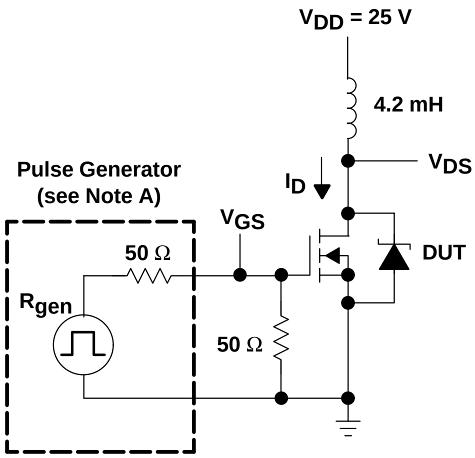


TEST CIRCUIT

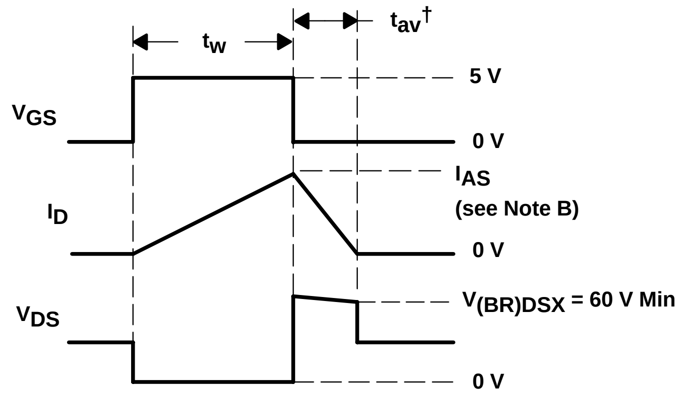
VOLTAGE WAVEFORM

Figure 3. Gate-Charge Test Circuit and Voltage Waveform

PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT



VOLTAGE AND CURRENT WAVEFORMS

† Non-JEDEC symbol for avalanche time

NOTES: A. The pulse generator has the following characteristics: $t_r \leq 10$ ns, $t_f \leq 10$ ns, $Z_O = 50\ \Omega$.

B. Input pulse duration (t_w) is increased until peak current $I_{AS} = 2.25$ A.

Energy test level is defined as $E_{AS} = \frac{I_{AS} \times V_{(BR)DSX} \times t_{av}}{2} = 19$ mJ, where t_{av} = avalanche time.

Figure 4. Single-Pulse Avalanche Energy Test Circuit and Waveforms

TYPICAL CHARACTERISTICS

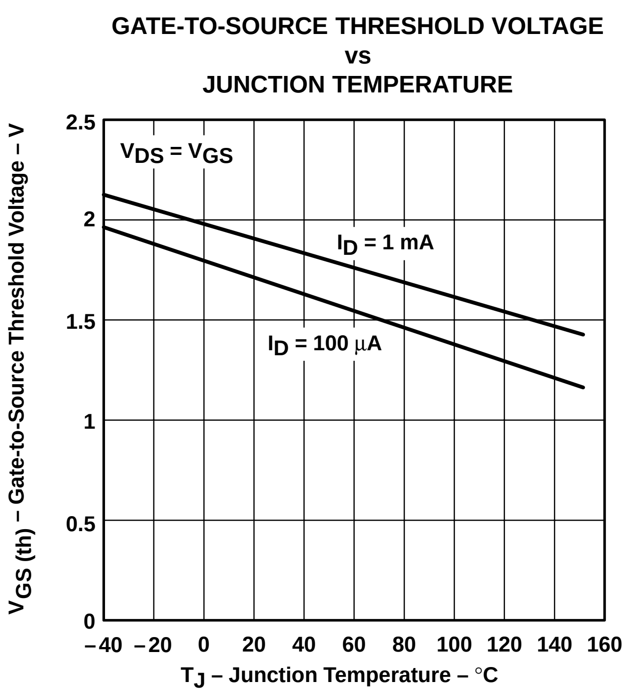


Figure 5

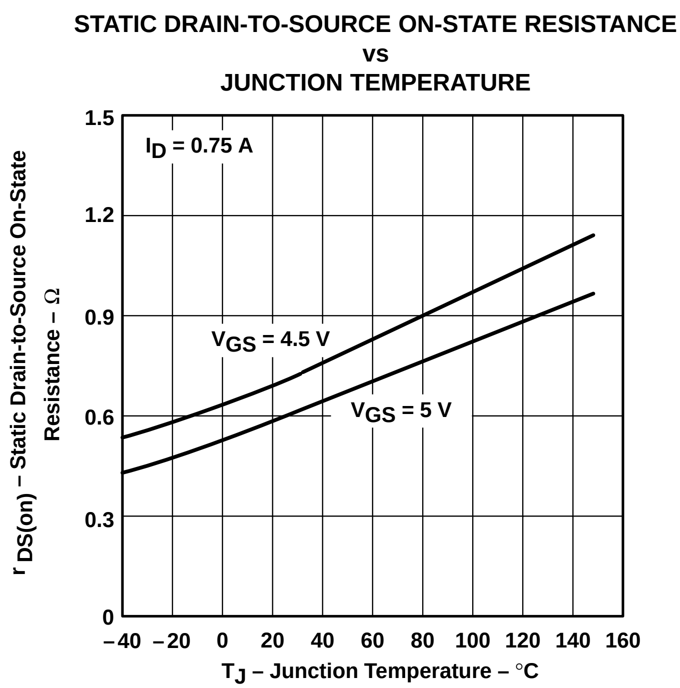


Figure 6

TYPICAL CHARACTERISTICS

STATIC DRAIN-TO-SOURCE ON-STATE RESISTANCE vs DRAIN CURRENT

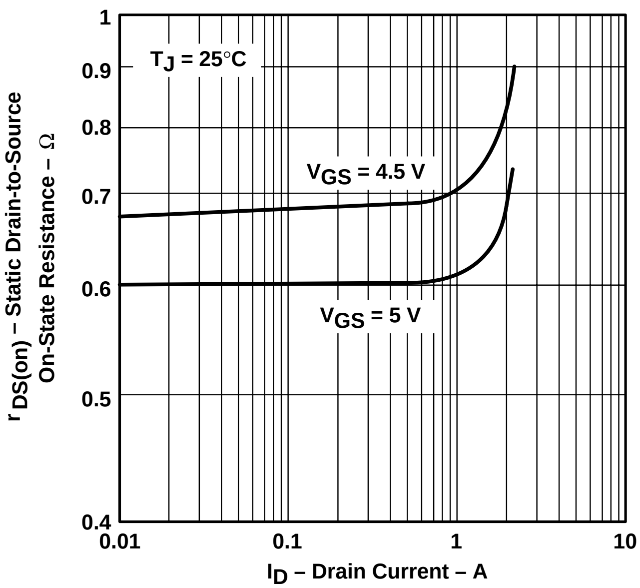


Figure 7

DRAIN CURRENT vs DRAIN-TO-SOURCE VOLTAGE

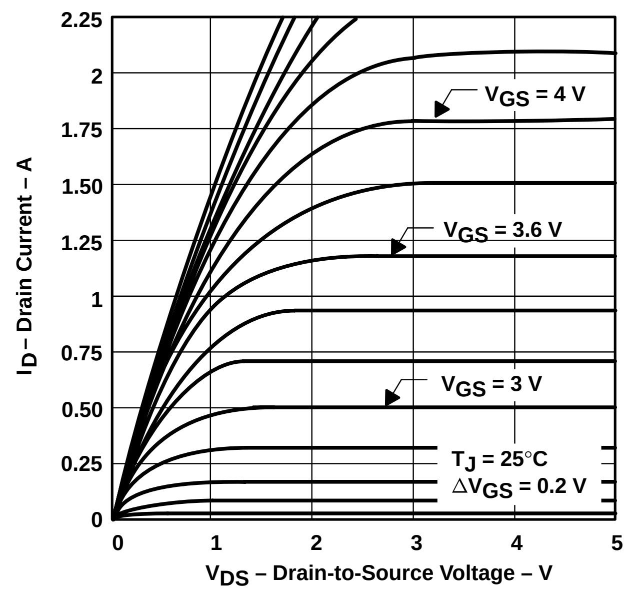


Figure 8

DISTRIBUTION OF FORWARD TRANSCONDUCTANCE

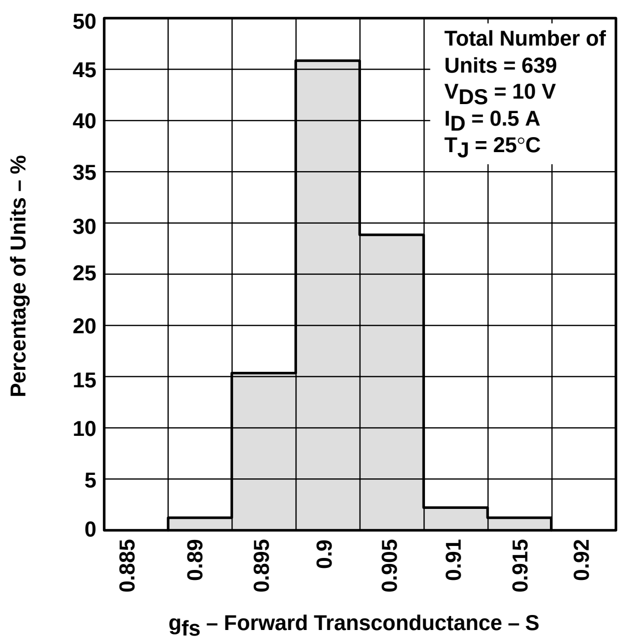


Figure 9

DRAIN CURRENT vs GATE-TO-SOURCE VOLTAGE

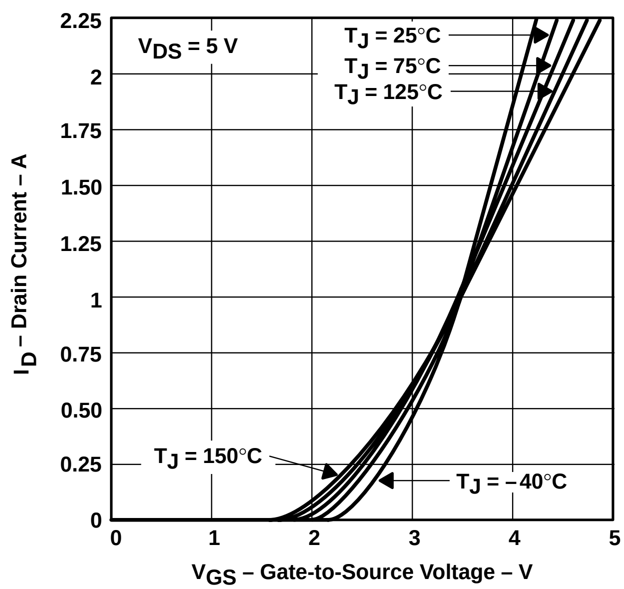


Figure 10

TYPICAL CHARACTERISTICS

CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

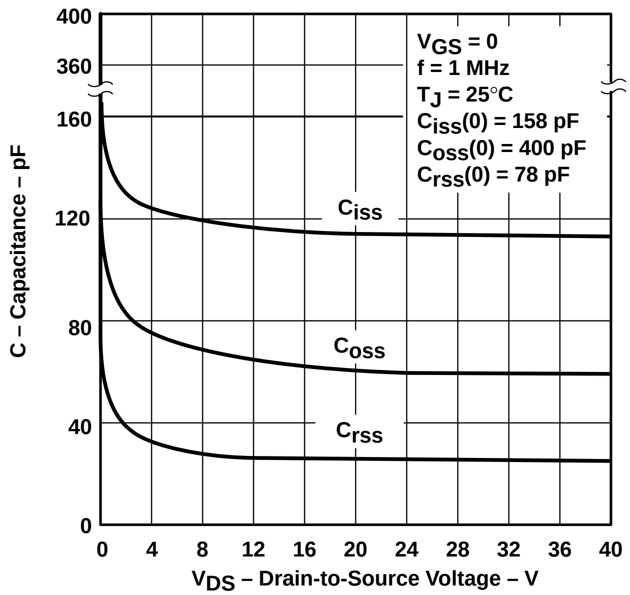


Figure 11

SOURCE-TO-DRAIN DIODE CURRENT vs SOURCE-TO-DRAIN VOLTAGE

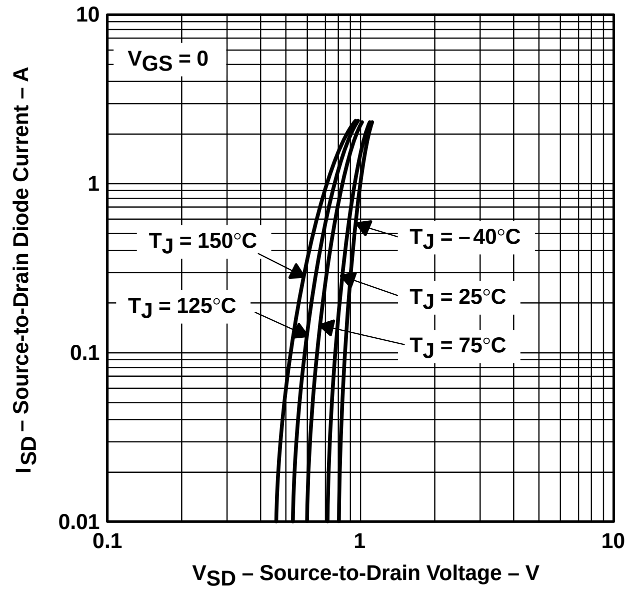


Figure 12

DRAIN-TO-SOURCE AND GATE-TO-SOURCE VOLTAGE vs GATE CHARGE

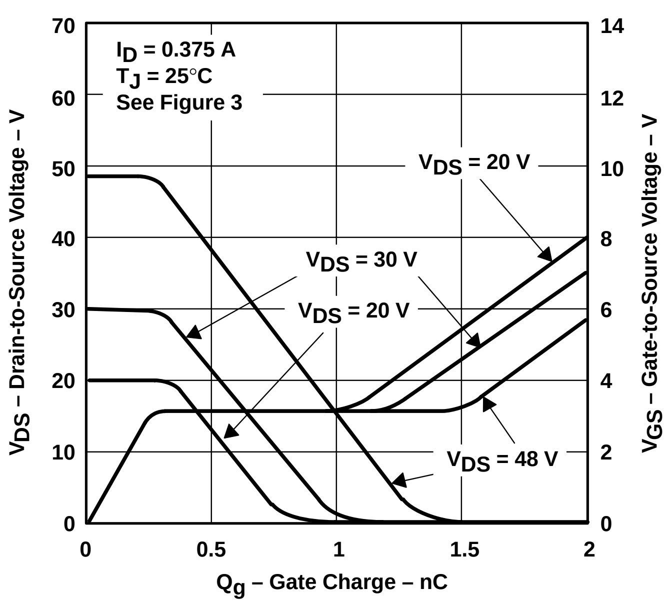


Figure 13

REVERSE-RECOVERY TIME vs REVERSE di/dt

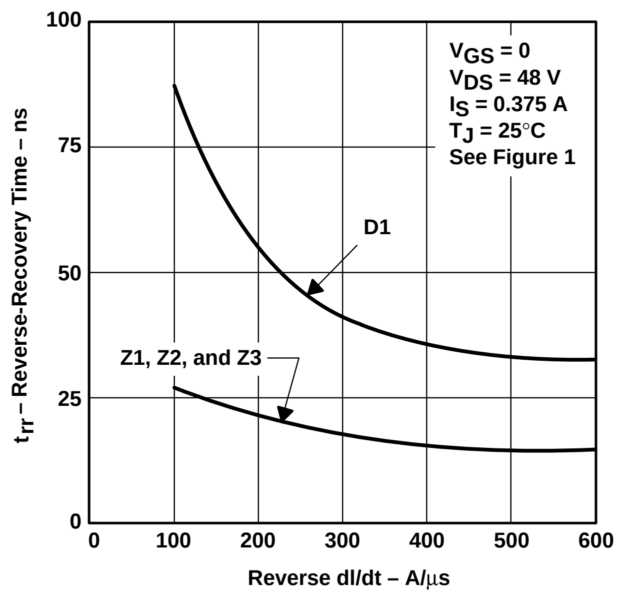
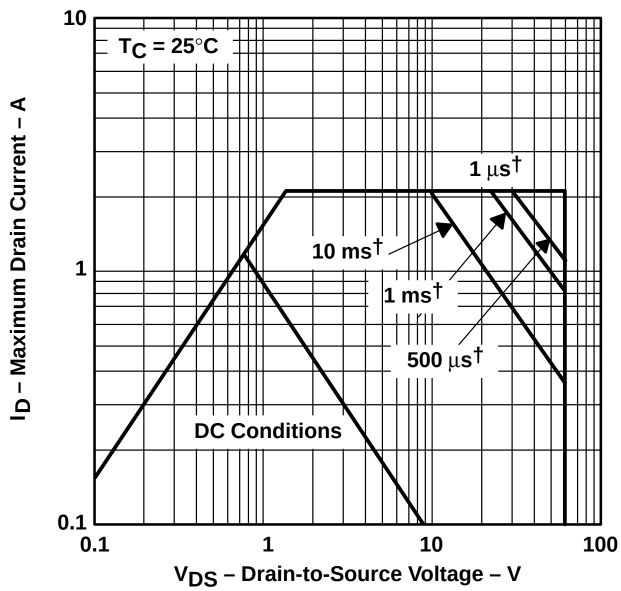


Figure 14

THERMAL INFORMATION

MAXIMUM DRAIN CURRENT vs DRAIN-TO-SOURCE VOLTAGE



† Less than 2% duty cycle

Figure 15

MAXIMUM PEAK AVALANCHE CURRENT vs TIME DURATION OF AVALANCHE

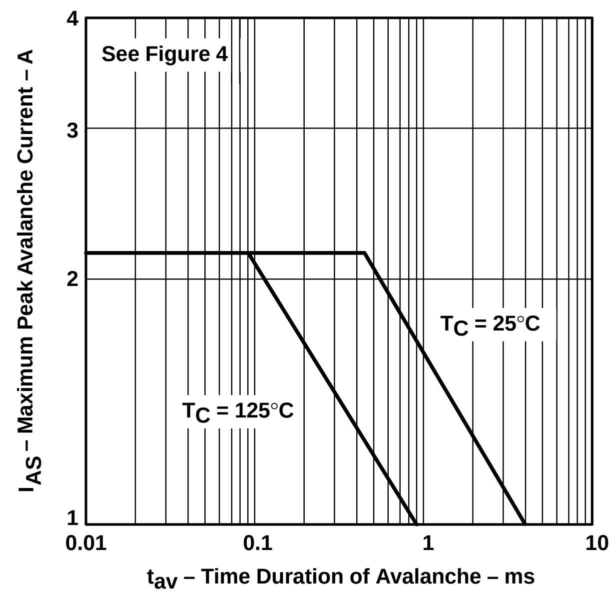
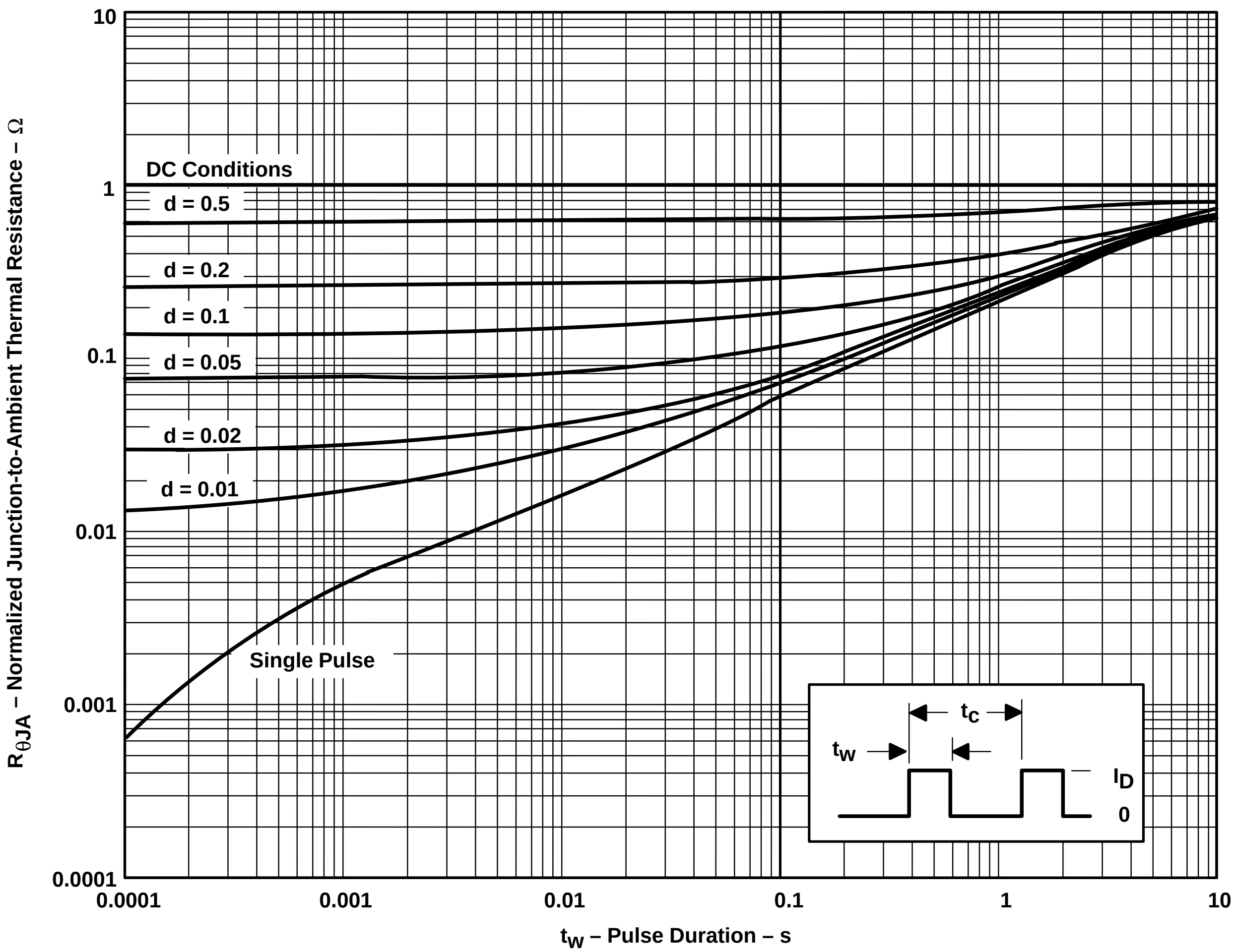


Figure 16

THERMAL INFORMATION

NORMALIZED JUNCTION-TO-AMBIENT THERMAL RESISTANCE†
vs
PULSE DURATION



† Device mounted on FR4 printed-circuit board with no heat sink.

NOTE A: $Z_{\theta A}(t) = r(t) R_{\theta JA}$
t_W = pulse duration
t_C = cycle time
d = duty cycle = t_W/t_C

Figure 17